

Title (en)

METHOD OF MANUFACTURING SEMICONDUCTOR ELEMENTS, IN PARTICULAR DIODES

Title (de)

VERFAHREN ZUR HERSTELLUNG VON HALBLEITERELEMENTEN, INSBESONDERE VON DIODEN

Title (fr)

PROCEDE POUR LA FABRICATION D'ELEMENTS SEMICONDUCTEURS, EN PARTICULIER DE DIODES

Publication

EP 0557318 B1 19970305 (DE)

Application

EP 91918830 A 19911107

Priority

- DE 4036222 A 19901114
- DE 9100863 W 19911107

Abstract (en)

[origin: WO9209099A1] The invention concerns a method of manufacturing semiconductor elements, in particular diodes, in which at least two semiconductor bodies are joined together. In order to obtain fully functioning, in particularly with diode characteristics, in simple fashion, one of the semiconductor bodies (10') has a high conductivity of one conductivity type, while the other semiconductor body (10') contains at least two layers of different doping density, at least one being of the opposite conductivity type to that of the first semiconductor body and the semiconductor bodies being bonded together using SFB techniques.

IPC 1-7

H01L 21/18; H01L 25/07; H01L 21/98

IPC 8 full level

H01L 21/329 (2006.01); **H01L 21/18** (2006.01); **H01L 21/98** (2006.01); **H01L 25/07** (2006.01)

CPC (source: EP)

H01L 21/187 (2013.01); **H01L 25/074** (2013.01); **H01L 25/50** (2013.01); **H01L 2924/0002** (2013.01)

Cited by

CN103700712A

Designated contracting state (EPC)

DE FR GB IT

DOCDB simple family (publication)

WO 9209099 A1 19920529; DE 4036222 A1 19920521; DE 59108592 D1 19970410; EP 0557318 A1 19930901; EP 0557318 B1 19970305; JP H06502277 A 19940310

DOCDB simple family (application)

DE 9100863 W 19911107; DE 4036222 A 19901114; DE 59108592 T 19911107; EP 91918830 A 19911107; JP 51710591 A 19911107